COMPLETE LISTING OF CLAIMS

IN ASCENDING ORDER WITH STATUS INDICATOR

1.-59. (Cancelled).

60. (original) A non-volatile resistance variable device comprising:

a substrate having a first electrode formed thereover;

a resistance variable chalcogenide material having metal ions diffused therein received operatively adjacent the first electrode;

a second electrode received operatively adjacent the resistance variable chalcogenide material; and

an actinic energy blocking material layer received on the second electrode to a thickness of no greater than 500 Angstroms.

61. (original) The device of claim 60 configured as a programmable memory cell.

62. (original) The device of claim 60 wherein the actinic energy blocking material is actinic energy reflective.

63. (original) The device of claim 60 wherein the actinic energy blocking material is actinic energy absorptive.

64. (original) The device of claim 60 wherein the actinic energy blocking material is insulative.

65. (original) The device of claim 60 wherein the actinic energy blocking material is conductive.

66. (original) The device of claim 60 wherein the actinic energy blocking material is selected from the group consisting of amorphous silicon, silicon oxynitride, silicon rich silicon nitride, and silicon rich silicon dioxide, and mixtures thereof.

67. (original) The device of claim 60 wherein the actinic energy blocking material is selected from the group consisting of tungsten and tungsten nitride, and silicon rich silicon dioxide, and mixtures thereof.

68. (original) A non-volatile resistance variable device comprising:

a substrate having a first electrode formed thereover;

a resistance variable chalcogenide material having metal ions diffused therein received operatively adjacent the first electrode;

a second electrode received operatively adjacent the resistance variable chalcogenide material; and

a substantially homogenous actinic energy blocking material layer received on the second electrode.

69. (original) The device of claim 68 configured as a programmable memory cell.

70. (currently amended) The ~~method~~ device of claim 68 wherein the actinic energy blocking material is actinic energy reflective.

71. (currently amended) The ~~method~~ device of claim 68 wherein the actinic energy blocking material is actinic energy absorptive.

72. (original) The device of claim 68 wherein the actinic energy blocking material is insulative.

73. (original) The device of claim 68 wherein the actinic energy blocking material is conductive.

74. (original) The device of claim 68 wherein the actinic energy blocking material layer has a thickness no greater than 500 Angstroms.

75. (original) The device of claim 68 wherein the actinic energy blocking material is selected from the group consisting of amorphous silicon, silicon oxynitride, silicon rich silicon nitride, and silicon rich silicon dioxide.

76. (original) The device of claim 68 wherein the actinic energy blocking material is selected from the group consisting of tungsten and tungsten nitride.

77. (original) A non-volatile resistance variable device comprising:

a substrate having a first electrode formed thereover;

a resistance variable chalcogenide material having metal ions diffused therein received operatively adjacent the first electrode;

a second electrode received operatively adjacent the resistance variable chalcogenide material; and

a first layer of material received on the second electrode to a thickness of no greater than 500 Angstroms, the material being selected from the group consisting of amorphous silicon, silicon oxynitride, silicon rich silicon nitride, silicon rich silicon dioxide, tungsten and tungsten nitride, and mixtures thereof.

78. (original) The device of claim 77 configured as a programmable memory cell.

79. (original) A non-volatile resistance variable device comprising:

a substrate having a first electrode formed thereover;

a resistance variable chalcogenide material having metal ions diffused therein received operatively adjacent the first electrode;

a second electrode received operatively adjacent the resistance variable chalcogenide material; and

a first homogeneous layer of material received on the second electrode, the material being selected from the group consisting of amorphous silicon, silicon oxynitride, silicon rich silicon nitride, silicon rich silicon dioxide, tungsten and tungsten nitride, and mixtures thereof.

80. (original) The device of claim 79 configured as a programmable memory cell.